Graphene based transversal-gated field effect transistor due to band gap modulation

S. Bala Kumar†, T. Fujita and Gengchiau Liang†
Department of Electrical and Computer Engineering, National University of Singapore, Singapore
Phone: +65-6516-2898 E-mail: brajahari@gmail.com and elelg@nus.edu.sg

1. Introduction
Neutral graphene is a zero band gap semimetal whose valence and conduction bands touch at the Brillouin zone corners. This fact makes pure graphene unsuitable for use in electronic device applications. Recently, the field has witnessed a concerted effort in the study of gapped graphene, e.g. via epitaxial growth on substrates [1], and application of top and back-gates (in graphene bilayers) [2]. Another promising method is via quantum confinement, e.g. in quasi one-dimensional strips of graphene known as graphene nanoribbons (GNRs). The energy band gap of GNRs is a strong function of their width and edge profile. For example, GNRs with armchair edges (AGNRs) generally exhibit semiconducting behavior, whilst zigzag GNRs are always metallic. Recently, it was also shown that the band structure of monolayer AGNRs can be varied by applying transversal potential [3]. With exploiting this effect, in this work, we introduce a transversal field effect transistor (FET) device (see Fig. 1). Unlike the conventional FET device whose gates are fabricated on top and bottom of the channel, transversal field effect transistors have the gates on the sides. Therefore, the channel layers can be stacked vertically as shown in Fig. 1(a), thus allowing multiple channels controlled by a single set of gates, resulting in a highly compact integration compared to conventional FET structure.

2. Simulation Model
We employ the nearest neighbor pi-orbital tight binding model [4] to study the electronics structure of a GNR. The Hamiltonian of a GNR is given by

\[ H = \sum_{n} V_{n} a_{n}^{\dagger} a_{n} - \sum_{n,m} t_{nm} a_{n}^{\dagger} a_{m} \]

where \( V_{n} \) is the onsite energy at site \( n \) including the potential across through the channel caused by the transversal gates, and \( t_{nm} = t \approx 3\text{eV} \) is the hopping energy between two bonded atoms \( m \) and \( n \). Here \( a_{n}^{\dagger} (a_{n}) \) refers to the electron creation (annihilation) operator at atom \( n \). The electron transport of the GNR is studied using the non-equilibrium Green’s function (NEGF) formalism. The transmission across the GNR at energy \( E \) is

\[ T(E) = \text{trace} \left[ \Gamma_{S}(E)G^\ast(E)\Gamma_{D}(E)G(E) \right] \]

where \( G^\ast \) is the retarded Green’s Function of the device region, and \( \Gamma_{SD} \) denotes the coupling between the source (drain) with the GNRs. The current density across GNRs is given by

\[ J = \frac{e}{h} \int_{-\infty}^{\infty} T(E) \left[ f_{S}(E) - f_{D}(E) \right] dE / W \]

where \( f_{S(D)} \) is the source (drain) Fermi distribution function, and \( W \) is the GNR width.

3. Results and Discussion

Firstly, we study the variation of the band structure of AGNRs with transverse-gate potential, \( V_{g} \). The minimum distance between the valence band and conduction band decreases as \( V_{g} \) increases. Here, the AGNR width \( W=13 a_{0} \).

Fig. 1 (a) Structure of a transversal-gated FET, where multiple AGNR channels are stacked vertically. (b) Top-view of a channel layer - AGNR with two side gates of opposite polarity. We assume a linear potential drop across the transverse direction of the structure. Source and drain contacts are shown. Source-drain bias is \( \mu_{SD} = \mu_{S} - \mu_{D} \)

Fig. 2: Band structure variation of AGNRs with increasing gate potential, \( V_{g} \). The minimum distance between the valence band and conduction band decreases as \( V_{g} \) increases. Here, the AGNR width \( W=13a_{0} \).

Fig. 3: Band gap variation with increasing \( V_{g} \) for different widths. The inset shows the conductance when \( U_{g}=0.2 \) and 0.5 \( [W=16a_{0}] \). The conductance gap is decreased when \( V_{g}=0.5 \).

Finally, we study the variation of the band structure of AGNRs with transverse-gate potential, \( V_{g} \). Below, we considered semiconducting AGNRs with type I (total number of dimmers \( N_{D}=3p+1 \), where \( p \) is an integer) [5], since these AGNRs have the largest band gap when \( V_{g}=0 \). Fig. 2 shows the changes in band structure as \( V_{g} \) increases (throughout this work, \( V_{g} \) is expressed in units of \( eV \)). The minimum separation between the conduction and valence band, i.e. the
band gap ($E_g$), changes with increasing $V_{gs}$ due to the spectral shift of the conduction and valence band states at the edges. In Fig. 3, the variation of the band gap with increasing $V_{gs}$ for AGNRs with different widths are studied. We found that under a sufficiently high $V_{gs}$, the gap is close to zero, i.e. $E_g \approx 0$. This indicates that AGNR from a semiconductor transits to metallic by introducing the transversal electrical field. [3] It is also found that for larger widths $W$, $E_g$ starts to decrease and approaches zero at lower $V_{gs}$. Furthermore, the inset of Fig. 3 shows the change in band gap of the devices proposed in Fig. 1 under $V_{gs}=0.2$ and 0.5 when $W=16\alpha_t$. As $V_{gs}$ increases the conduction gap decreases corresponding to the decrease in $E_g$. As the conduction gap decreases the AGNR becomes more conducting, resulting in higher source-drain current ($J_{SD}$).

Fig. 4: Source drain linear current density, $J_{SD} \sim U_g$ for varying (a) AGNR width $W$, (b) temperature $Temp.$, and (c) source-drain bias $\mu_{sd}$. Unless otherwise stated: Temp.$=300K$, $W=19\alpha_t$, and $\mu_{sd}=0.01t$.

In Fig. 4 we present the variation of simulated $J_{SD}$ with increasing $V_{gs}$ under various conditions. All devices present the transistor behaviors with the ON and OFF states with the different $V_{gs}$ caused by bandgap modulation under the transversal electrical field. Fig. 4(a) shows the effect of AGNR width on $J_{SD}$. As the width increases, the $E_g$ under $V_{gs}=0$ decreases, resulting in lower OFF-$J_{SD}$. On the other hand, the ON-$J_{SD}$ remains same under different $W$. It is because at ON-state, $E_g \approx 0$ regardless of $W$. Moreover, the on-state is achieved at lower $V_{gs}$ for devices with larger width, since for larger $W$, the $E_g$ begins decreasing at lower $V_{gs}$ [cf., Fig. 3]. Next, we investigate the effect of temperature ($Temp.$) on $J_{SD}$ as shown in Fig. 4(b). Due to the spreading of the Fermi distribution function, under the high temperature, the OFF-$J_{SD}$ increases, and hence the performance of the transistor degrades. Fig. 4(c) shows the effect of source-drain bias, ($\mu_{sd}-\mu_{sd}$/e. As the bias increases, the conduction window is widened and thus, more electrons are transported in the device, resulting in higher OFF-currents and ON-currents.

Finally, we explore the edge vacancy effects on device characteristics. Interestingly, we find that the subthreshold slope (SS) can be further decreased, by defect engineering at the edges. Referring to Fig. 5, when we introduce vacancies at the top-edge (35%), the conduction gap increases in the OFF-state. It is because type I AGNR has the largest bandgap compared to the two types, and hence any fluctuation on the edge will increase the bandgap. However as $V_{gs}$ is increased, the conduction gap decreases at a higher rate in the disordered structure. This results in a lower OFF-$J_{SD}$ and smaller SS. The $J_{SD}$ curve with vacancies at the top edge is shown in Fig. 6. As predicted, the OFF-current and the SS are lower for the disordered AGNR transversal gate FETs and the ON-state can be reached at lower $V$ compared to the smooth-edge one. However, vacancies also suppress the magnitude of the conductance due to the scattering processes as shown in Fig. 6. Therefore, a careful engineering of the vacancies can optimize the performance of the transistor.

Fig. 5: The effect of vacancies at the top edge in modifying the conduction gap. (a) Conductance of a perfect structure, (b) conductance of disordered structure. Vacancies increase (decrease) the conduction gap when $V_{gs}=0$ ($V_{gs}$ is high). [$W=19\alpha_t$, Temp.$=300K$]

Fig. 6: Source-drain linear current density, $J_{SD} \sim U_g$ for varying source-drain bias, $\mu_{sd}$. Thick (thin) lines show the variation for a disordered (perfect) structure. The slope is enhanced due to vacancies. However, the off current is reduced.

4. Conclusion
In summary, we have explored the possibility and fundamental physics of a transversal-gated FET in which an asymmetric electrochemical potential is applied to the lateral edges of a monolayer AGNR. This potential causes a reduction in the band gap of the AGNR, thus resulting in larger current flow across the device. We found that the device performance can be improved by introducing vacancies at the top edge of the structure. Engineering of the device width and vacancies play an important role in optimizing the device performance.

References